

NCE N-Channel Enhancement Mode Power MOSFET

Description

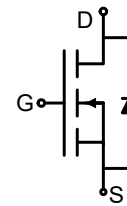
The NCE0102 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

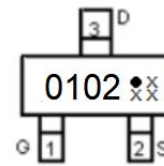
- $V_{DS} = 100V, I_D = 2A$
 $R_{DS(ON)} < 220m\Omega @ V_{GS}=10V$ (Typ:190m Ω)
 $R_{DS(ON)} < 240m\Omega @ V_{GS}=4.5V$ (Typ:200m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
0102 $\times\times$	NCE0102	SOT-23	$\varnothing 180mm$	8 mm	3000 units

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	2	A
Drain Current-Continuous($T_C=100^\circ C$)	$I_D(100^\circ C)$	1.4	A
Drain Current-Pulsed (Note 1)	I_{DM}	8	A
Maximum Power Dissipation	P_D	1.25	W
Avalanche Current (Note 1)	I_{AR}	2	A
Single pulse avalanche energy (Note 5)	E_{AS}	2.45	mJ
Reverse diode dv/dt , $V_{DS} \leq 80V$, $I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	$^\circ C/W$
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Electrical Characteristics (T_A=25°C unless otherwise noted)

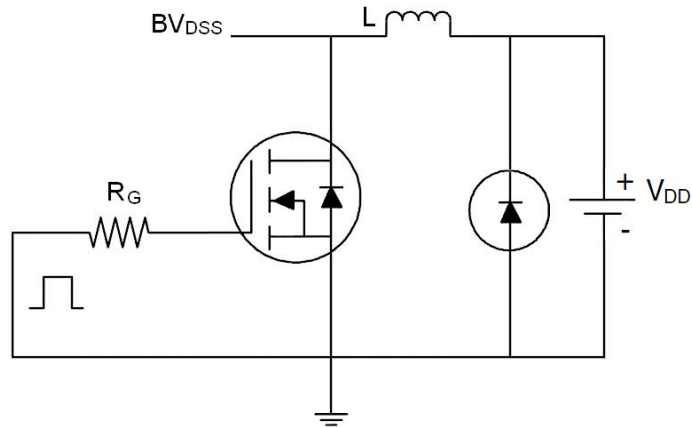
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100	110	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =2A	-	190	220	mΩ
		V _{GS} =4.5V, I _D =2A	-	200	240	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =2A	1	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	360.6	-	PF
Output Capacitance	C _{oss}		-	24.6	-	PF
Reverse Transfer Capacitance	C _{rss}		-	13	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, R _L =25Ω V _{GS} =10V, R _G =1Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	10	-	nS
Turn-Off Delay Time	t _{d(off)}		-	12	-	nS
Turn-Off Fall Time	t _f		-	8	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =2A, V _{GS} =10V	-	12.0	-	nC
Gate-Source Charge	Q _{gs}		-	1.8	-	nC
Gate-Drain Charge	Q _{gd}		-	2.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =2A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	2	A

Notes:

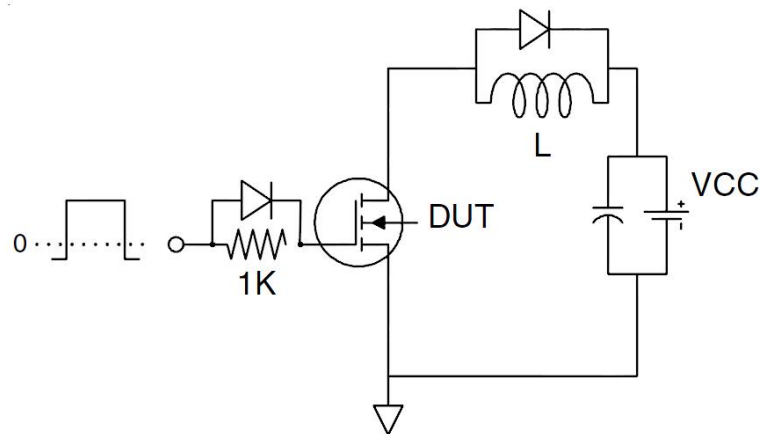
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_j=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω

Test Circuit

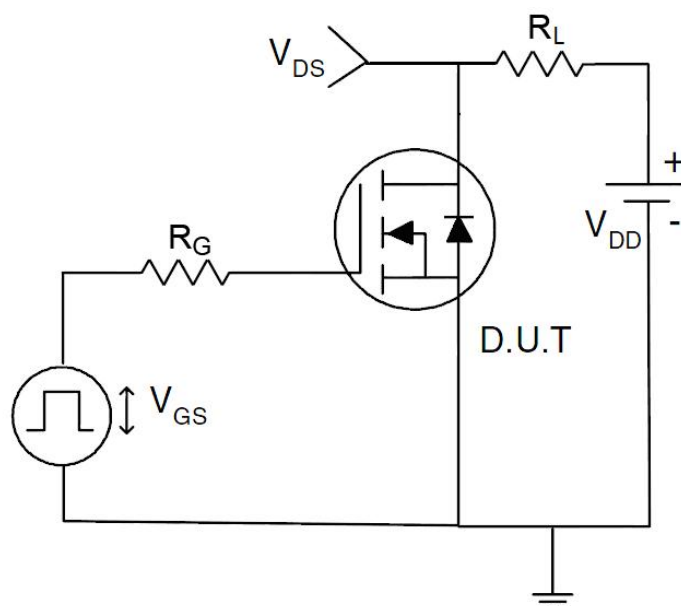
1) EAS test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

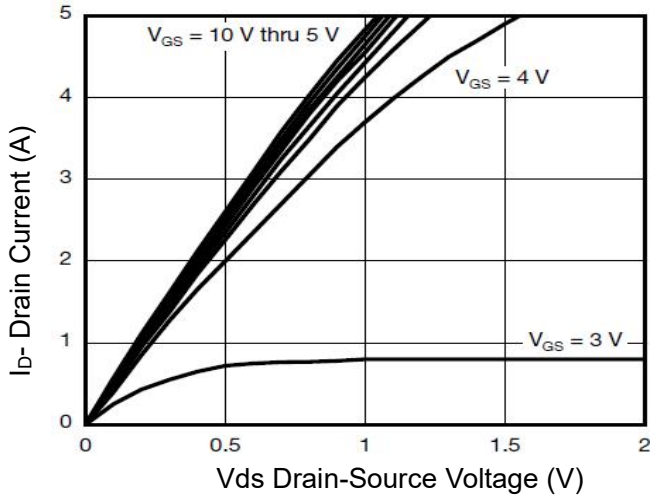


Figure 1 Output Characteristics

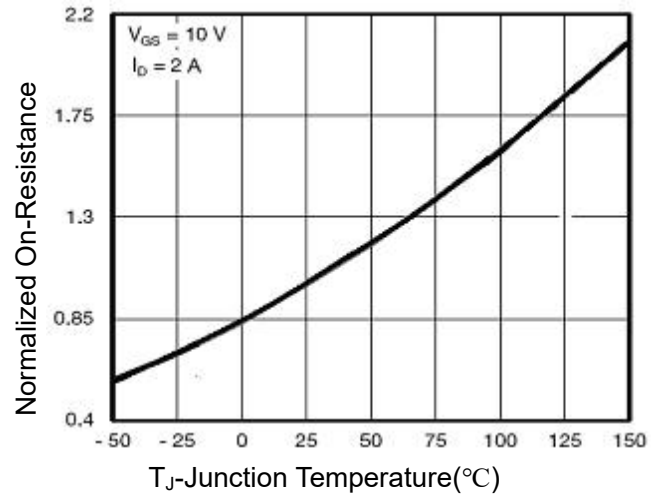


Figure 4 Rdson-Junction Temperature

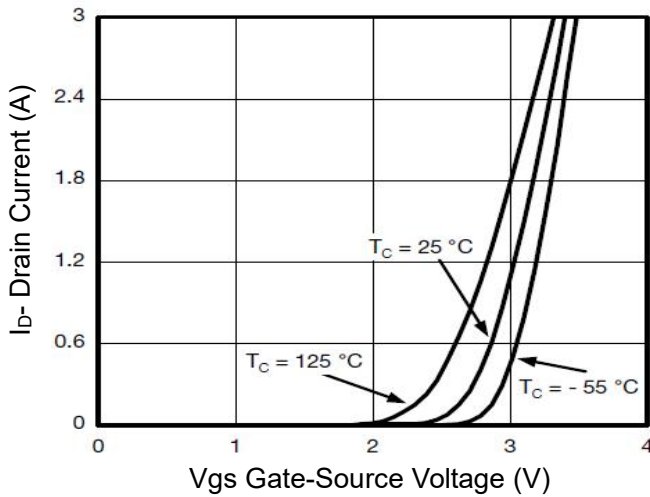


Figure 2 Transfer Characteristics

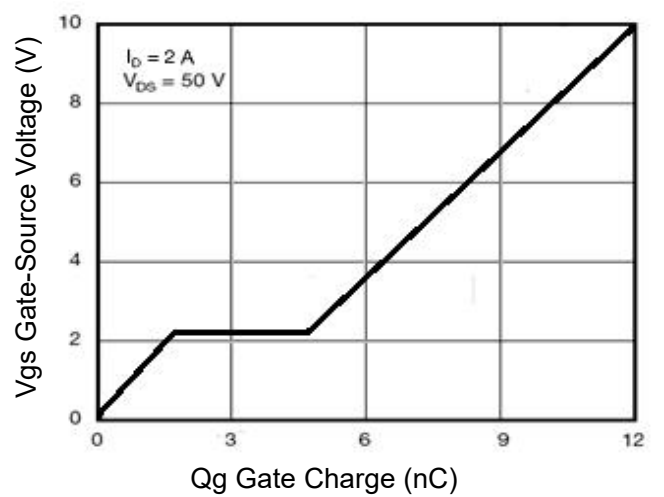


Figure 5 Gate Charge

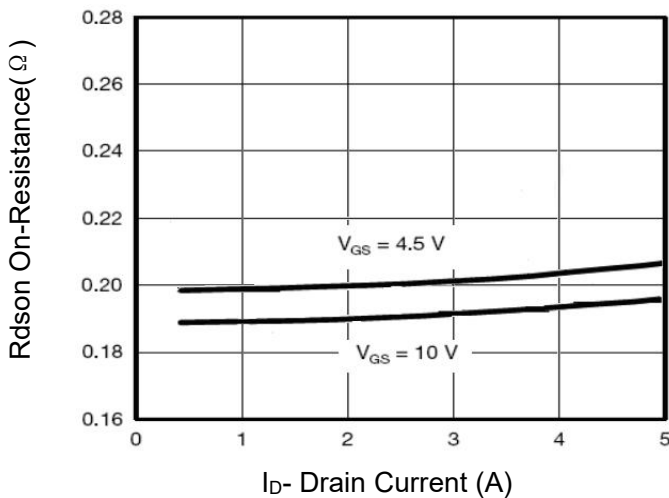


Figure 3 Rdson- Drain Current

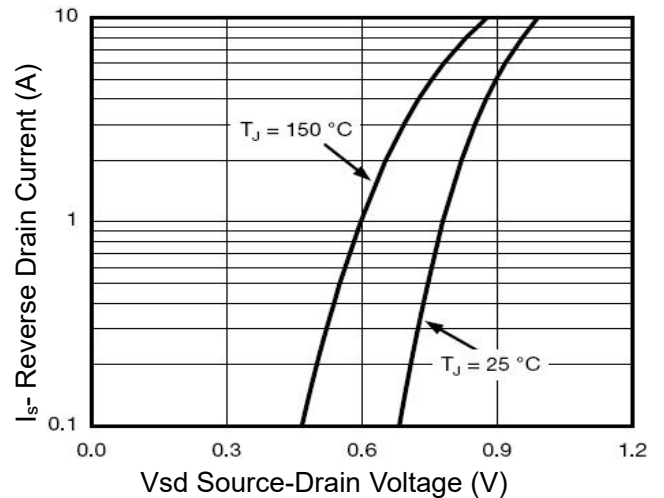


Figure 6 Source- Drain Diode Forward

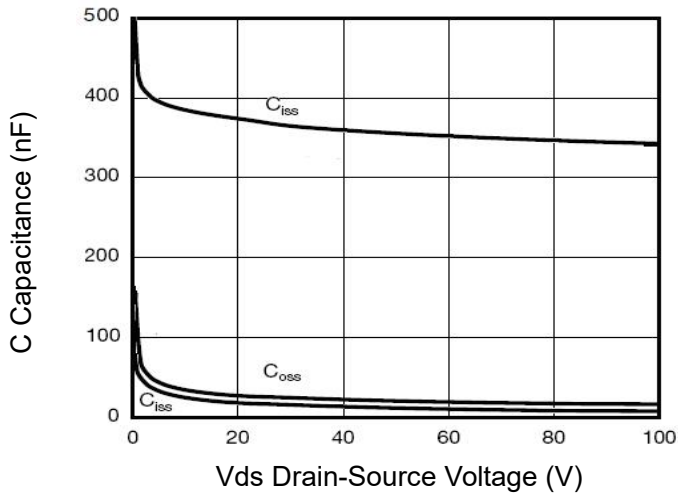


Figure 7 Capacitance vs Vds

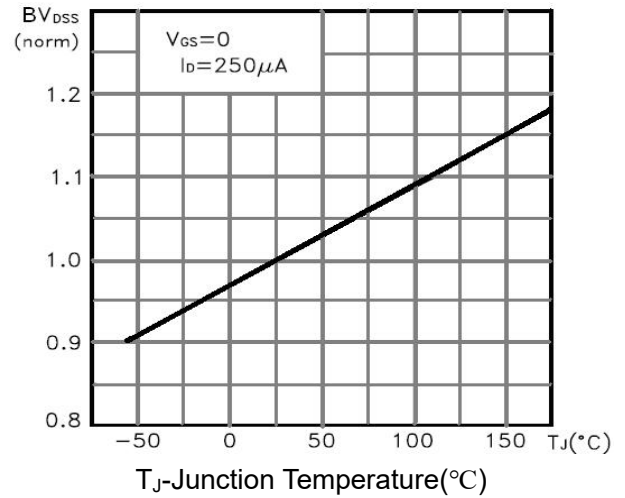


Figure 9 BV_{DSS} vs Junction Temperature

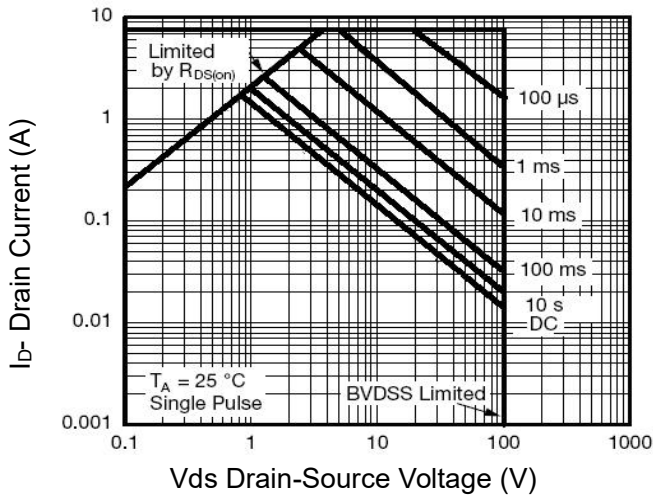


Figure 8 Safe Operation Area

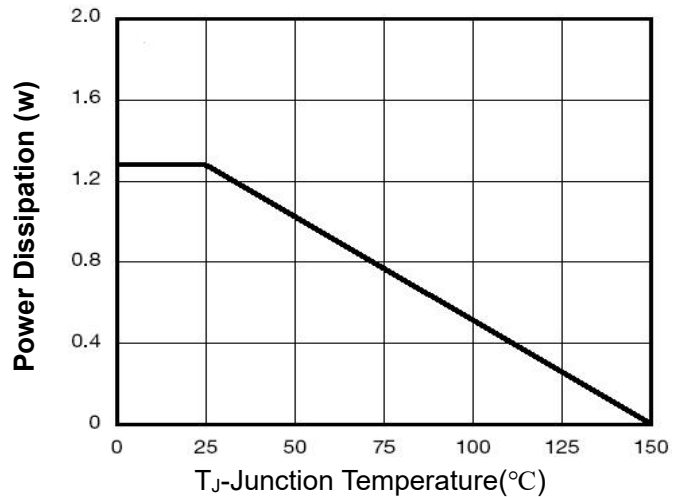


Figure 10 Power De-rati

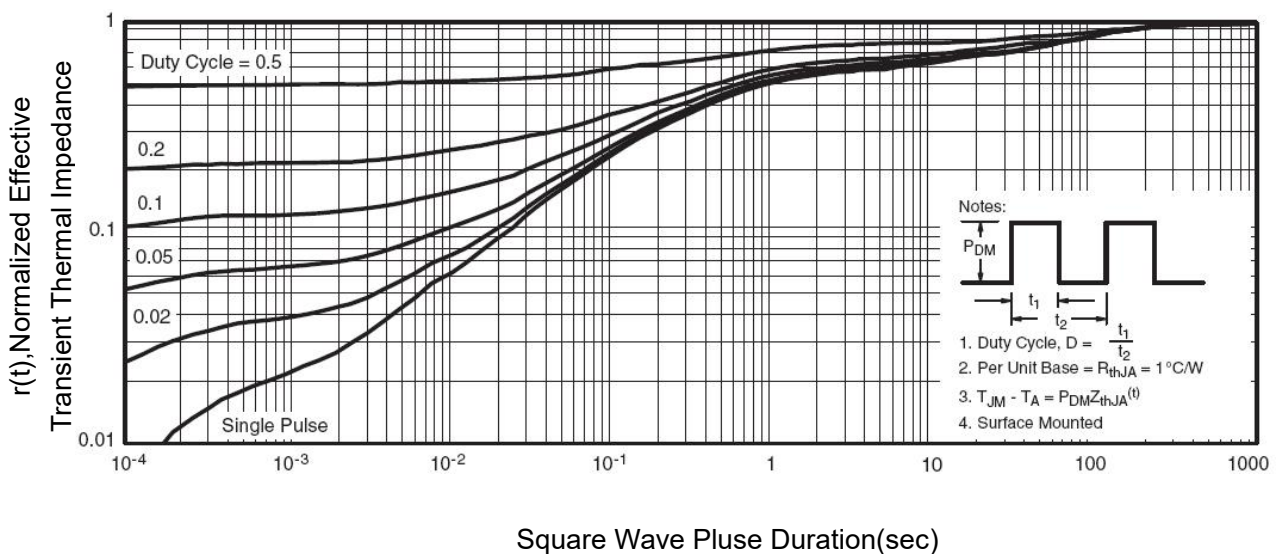
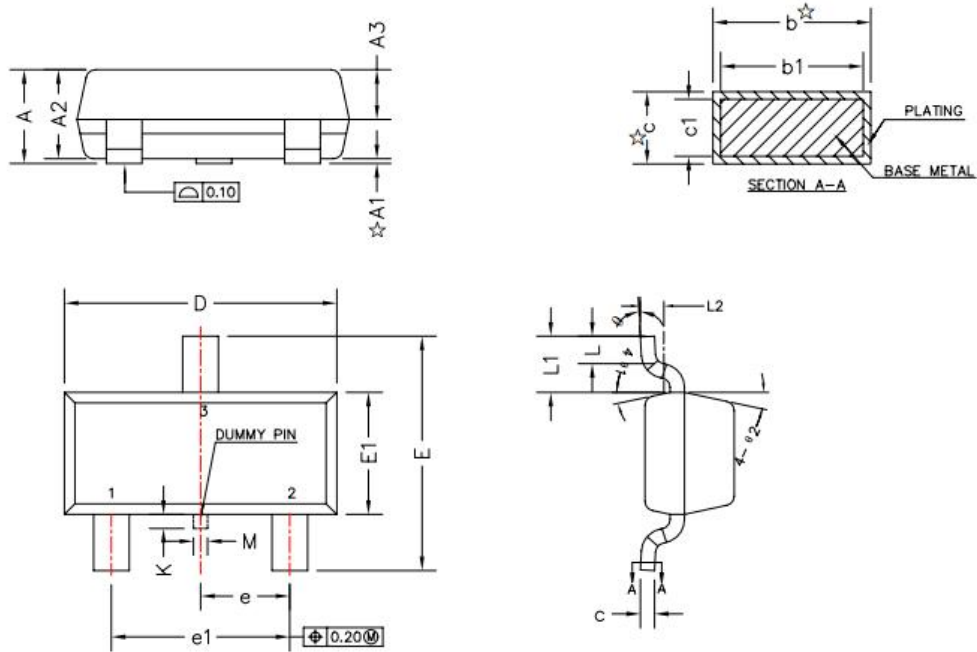


Figure 11 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Information



Symbol	Millimeters	
	Min.	Max.
A	0.89	1.12
A1	0.01	0.10
A2	0.88	1.02
A3	0.43	0.63
b	0.36	0.50
b1	0.35	0.45
c	0.14	0.20
c1	0.14	0.16
D	2.80	3.00
E	2.35	2.64
E1	1.20	1.40
e	0.90	1.00
e1	1.80	2.00
L	0.40	0.60
L1	0.6REF	
L2	0.25BSC	
M	0.10	0.25
K	0.00	0.25
θ	0°	8°
θ_1	10°	14°
θ_2	10°	14°

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